TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC2982

Storobo Flash Applications Medium Power Amplifier Applications

• High DC current gain and excellent linearity

: $h_{FE}(1) = 140 \text{ to } 600 \text{ (V}_{CE} = 1 \text{ V, I}_{C} = 0.5 \text{ A})$

 $h_{FE}(2) = 70 \text{ (min)}, 140 \text{ (typ.)}, (V_{CE} = 1 \text{ V}, I_{C} = 2 \text{ A})$

• Low saturation voltage

: $V_{CE (sat)} = 0.5 V (max) (I_{C} = 2 A, I_{B} = 50 mA)$

• Small flat package

• PC = 1.0 to 2.0 W (mounted on a ceramic substrate)

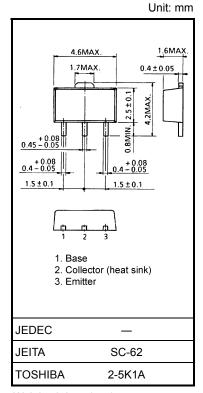
• Complementary to 2SA1314

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	30	V	
Collector-emitter voltage		V _{CES}	30	V	
		V_{CEO}	10		
Emitter-base voltage		V _{EBO}	6	V	
Collector current	DC	Ic	2	А	
	Pulse (Note 1)	I _{CP}	4		
Base current	DC	Ι _Β	0.4	Α	
	Pulse (Note 1)	I _{BP}	0.8		
Collector power dissipation		PC	500	mW	
		P _C	1000		
		(Note 2)	1000		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	−55 to 150	°C	

Note 1: Pulse test: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: 2SC2982 mounted on a ceramic substrate (250 mm² × 0.8 t)



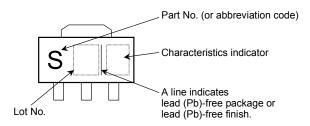
Weight: 0.05 g (typ.)

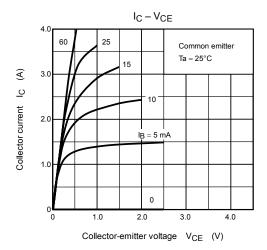
Electrical Characteristics (Ta = 25°C)

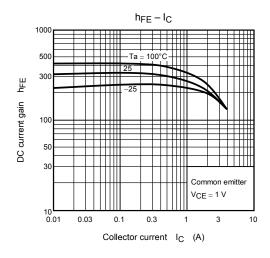
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 30 V, I _E = 0	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C = 0	_	_	0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	10	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	I _E = 1 mA, I _C = 0	6	_	_	V
DC current gain	h _{FE (1)} (Note 3)	V _{CE} = 1 V, I _C = 0.5 A	140	_	600	_
	h _{FE (2)}	V _{CE} = 1 V, I _C = 2 A	70	140	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 2 A, I _B = 50 mA	_	0.2	0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 1 V, I _C = 2 A	_	0.86	1.5	V
Transition frequency	f _T	V _{CE} = 1 V, I _C = 0.5 A	_	150	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	27	_	pF

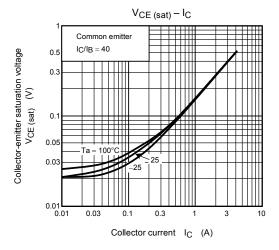
Note 3: hFE (1) classification A: 140 to 240, B: 200 to 330, C: 300 to 450, D: 420 to 600

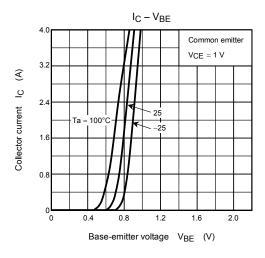
Marking

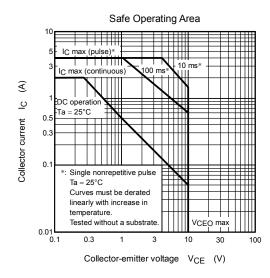


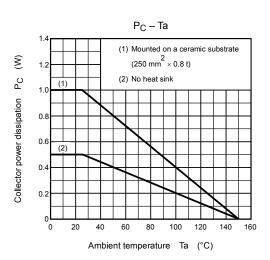












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